

FAN7371

High-Current High-Side Gate Drive IC

Features

- Floating Channel for Bootstrap Operation to +600V
- 4A/4A Sourcing/Sinking Current Driving Capability
- Common-Mode dv/dt Noise Canceling Circuit
- 3.3V and 5V Input Logic Compatible
- Output In-phase with Input Signal
- Under- Voltage Lockout for V_{BS}
- 25V Shunt Regulator on V_{DD} and V_{BS}
- 8-Lead Small Outline Package (SOP)

Applications

- High-Speed Gate Driver
- Sustain Switch Driver in PDP Application
- Energy-Recovery Circuit Switch Driver in PDP Application
- High-Power Buck Converter
- Motor Drive Inverter

Description

The FAN7371 is a monolithic high-side gate drive IC, which can drive high-speed MOSFETs and IGBTs that operate up to +600V. It has a buffered output stage with all NMOS transistors designed for high pulse current driving capability and minimum cross-conduction.

Fairchild's high-voltage process and common-mode noise canceling techniques provide stable operation of the high-side driver under high dv/dt noise circumstances. An advanced level-shift circuit offers high-side gate driver operation up to $V_S = -9.8V$ (typical) for $V_{BS} = 15V$.

The UVLO circuit prevents malfunction when V_{BS} is lower than the specified threshold voltage.

The high-current and low-output voltage drop feature makes this device suitable for sustain and energy recovery circuit switches driver in the Plasma Display Panel application, motor drive inverter, switching power supply, and high-power DC-DC converter applications.

8-SOP

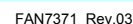


Ordering Information

Part Number	Package	Pb-Free	Operating Temperature Range	Packing Method
FAN7371M	8-SOP	Yes	-40°C ~ 125°C	TUBE
FAN7371MX				TAPE & REEL

Note:

- 1 These devices passed wave soldering test by JESD22A-111.



The schematic diagram illustrates the FAN7371 inverter circuit. The power supply is 15V, connected to the V_{DD} pin (pin 1) and the bootstrap network (R_{BOOT}, D_{BOOT}). The bootstrap network is connected to the V_B pin (pin 8). The PWM input is connected to the IN pin (pin 2). The GND pin (pin 4) is connected to the common ground. The V_S pin (pin 6) is connected to the MOSFET driver network (R1, R2, C_{BOOT}). The MOSFET driver network is connected to the HO pin (pin 7). The MOSFET is connected to the output filter (L1, C2) and the output voltage V_{OUT}. The output filter is connected to the output voltage V_{OUT}. The output voltage V_{OUT} is measured across the output filter capacitor C2.

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Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. $T_A=25^{\circ}\text{C}$ unless otherwise specified.

Symbol	Characteristics	Min.	Max.	Unit
V_S	High-Side Floating Offset Voltage	$V_B - V_{SHUNT}$	$V_B + 0.3$	V
V_B	High-Side Floating Supply Voltage ⁽²⁾	-0.3	625.0	V
V_{HO}	High-Side Floating Output Voltage	$V_S - 0.3$	$V_B + 0.3$	V
V_{DD}	Low-Side and Logic Supply Voltage ⁽²⁾	-0.3	V_{SHUNT}	V
V_{IN}	Logic Input Voltage	-0.3	$V_{DD} + 0.3$	V
dV_S/dt	Allowable Offset Voltage Slew Rate		± 50	V/ns
P_D	Power Dissipation ^(3, 4, 5)		0.625	W
θ_{JA}	Thermal Resistance		200	$^{\circ}\text{C}/\text{W}$
T_{JMAX}	Maximum Junction Temperature		150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-55	150	$^{\circ}\text{C}$

Notes:

- This IC contains a shunt regulator on V_{DD} and V_{BS} with a normal breakdown voltage of 25V. Please note that this supply pin should not be driven by a low-impedance voltage source greater than the V_{SHUNT} specified in the Electrical Characteristics section
- Mounted on 76.2 x 114.3 x 1.6mm PCB (FR-4 glass epoxy material).
- Refer to the following standards:
JESD51-2: Integral circuits thermal test method environmental conditions, natural convection, and
JESD51-3: Low effective thermal conductivity test board for leaded surface mount packages.
- Do not exceed power dissipation (P_D) under any circumstances.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min.	Max.	Unit
V_B	High-Side Floating Supply Voltage	$V_S + 10$	$V_S + 20$	V
V_S	High-Side Floating Supply Offset Voltage	$6 - V_{DD}$	600	V
V_{HO}	High-Side Output Voltage	V_S	V_B	V
V_{IN}	Logic Input Voltage	GND	V_{DD}	V
V_{DD}	Supply Voltage	10	20	V
T_A	Operating Ambient Temperature	-40	125	$^{\circ}\text{C}$

Electrical Characteristics

$V_{BIAS}(V_{DD}, V_{BS})=15.0V$, $T_A = 25^\circ C$, unless otherwise specified. The V_{IN} and I_{IN} parameters are referenced to GND. The V_O and I_O parameters are relative to V_S and are applicable to the respective output HO.

Symbol	Characteristics	Test Condition	Min.	Typ.	Max.	Unit
POWER SUPPLY SECTION						
I_{QDD}	Quiescent V_{DD} Supply Current	$V_{IN}=0V$ or $5V$		25	70	μA
I_{PDD}	Operating V_{DD} Supply Current	$f_{IN}=20KHz$, No Load		35	100	μA
BOOTSTRAPPED SUPPLY SECTION						
V_{BSUV+}	V_{BS} Supply Under-Voltage Positive Going Threshold Voltage	$V_{IN}=0V$, V_{BS} =Sweep	8.2	9.2	10.2	V
V_{BSUV-}	V_{BS} Supply Under-Voltage Negative Going Threshold Voltage	$V_{IN}=0V$, V_{BS} =Sweep	7.5	8.5	9.5	V
V_{BSHYS}	V_{BS} Supply Under-Voltage Lockout Hysteresis Voltage	$V_{IN}=0V$, V_{BS} =Sweep		0.7		V
I_{LK}	Offset Supply Leakage Current	$V_B=V_S=600V$			10	μA
I_{QBS}	Quiescent V_{BS} Supply Current	$V_{IN}=0V$ or $5V$		60	120	μA
I_{PBS}	Operating V_{BS} Supply Current	$C_{LOAD}=1000pF$, $f_{IN}=20KHz$, rms value		1.0	2.8	mA
SHUNT REGULATOR SECTION						
V_{SHUNT}	V_{DD} and V_{BS} Shunt Regulator Clamping Voltage	$I_{SHUNT}=5mA$	24	25		V
INPUT LOGIC Section						
V_{IH}	Logic "1" Input Voltage		2.5			V
V_{IL}	Logic "0" Input Voltage				0.8	V
I_{IN+}	Logic Input High Bias Current	$V_{IN}=5V$		45	70	μA
I_{IN-}	Logic Input Low Bias Current	$V_{IN}=0V$			2	μA
R_{IN}	Input Pull-down Resistance		70	110		$K\Omega$
GATE DRIVER OUTPUT SECTION						
V_{OH}	High-Level Output Voltage ($V_{BIAS} - V_O$)	No Load			1.2	V
V_{OL}	Low-Level Output Voltage	No Load			30	mV
I_{O+}	Output High, Short-Circuit Pulsed Current ⁽⁶⁾	$V_{HO}=0V$, $V_{IN}=5V$, $PW \leq 10\mu s$	3.0	4.0		A
I_{O-}	Output Low, Short-Circuit Pulsed Current ⁽⁶⁾	$V_{HO}=15V$, $V_{IN}=0V$, $PW \leq 10\mu s$	3.0	4.0		A
V_S	Allowable Negative V_S pin Voltage for IN Signal Propagation to HO			-9.8	-7.0	V

Note:

6 These parameters guaranteed by design.

Dynamic Electrical Characteristics

$V_{DD}=V_{BS}=15V$, $GND=0V$, $C_{LOAD}=1000pF$, $T_A=25^\circ C$, unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
t_{on}	Turn-on Propagation Delay Time	$V_S=0V$		150	210	ns
t_{off}	Turn-off Propagation Delay Time	$V_S=0V$		150	210	ns
t_r	Turn-on Rise Time			25	50	ns
t_f	Turn-off Fall Time			15	40	ns

Typical Characteristics

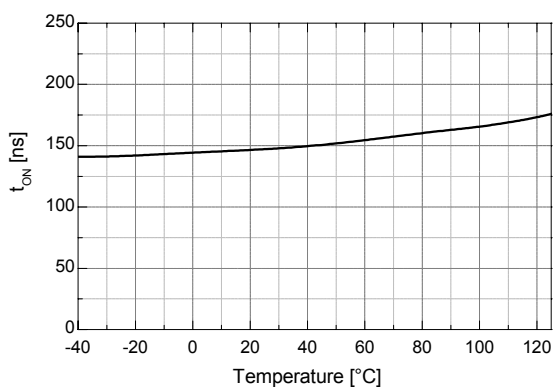


Figure 5. Turn-on Propagation Delay vs. Temp.

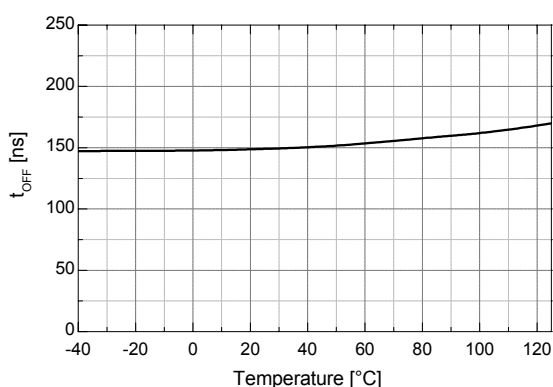


Figure 6. Turn-off Propagation Delay vs. Temp.

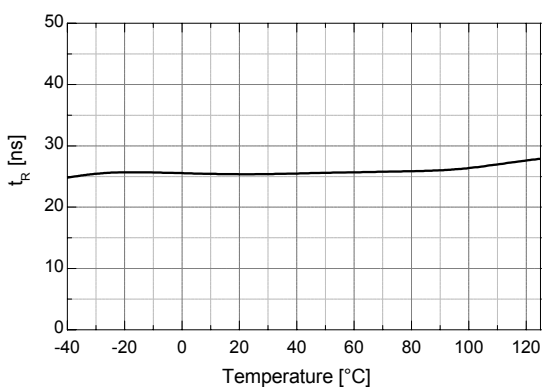


Figure 7. Turn-on Rise Time vs. Temp.

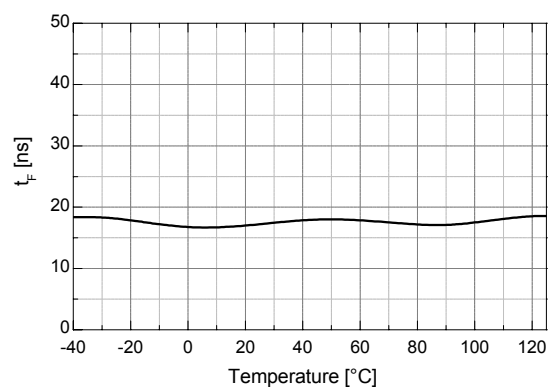


Figure 8. Turn-off Fall Time vs. Temp.

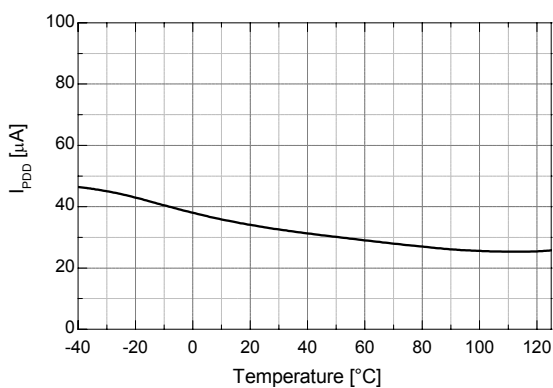


Figure 9. Operating V_{DD} Supply Current vs. Temp.

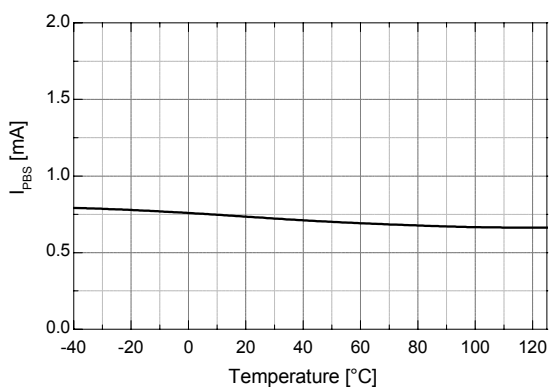


Figure 10. Operating V_{BS} Supply Current vs. Temp.

Typical Characteristics (Continued)

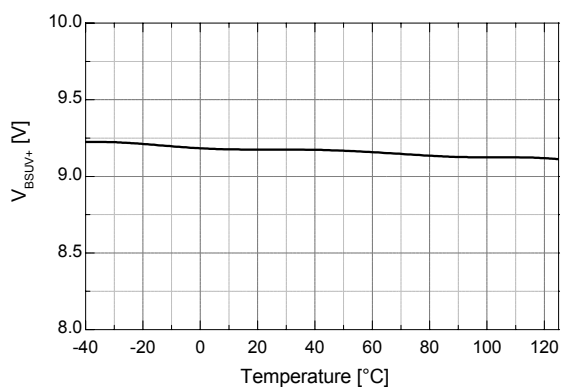
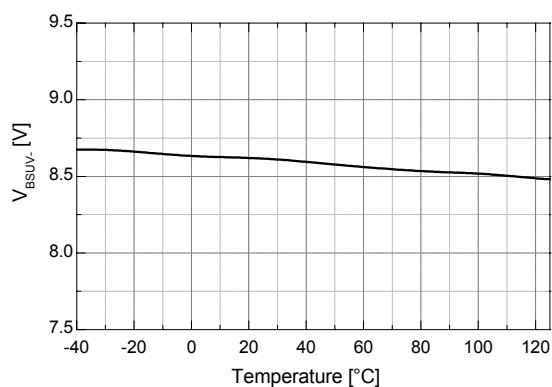
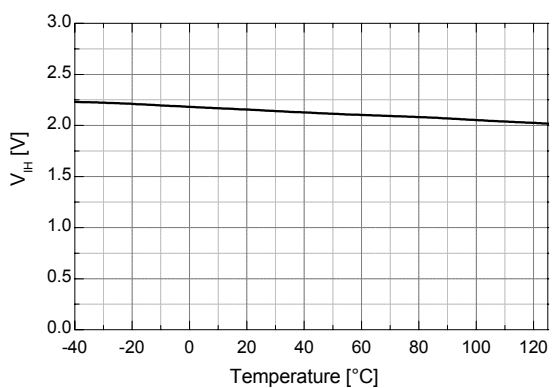
Figure 11. V_{BS} UVLO+ vs. Temp.Figure 12. V_{BS} UVLO- vs. Temp.

Figure 13. Logic High Input Voltage vs. Temp.

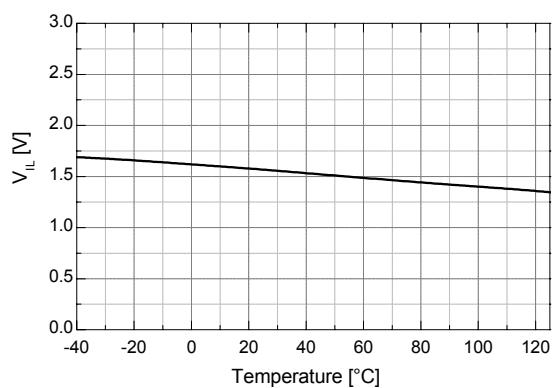


Figure 14. Logic Low Input Voltage vs. Temp.

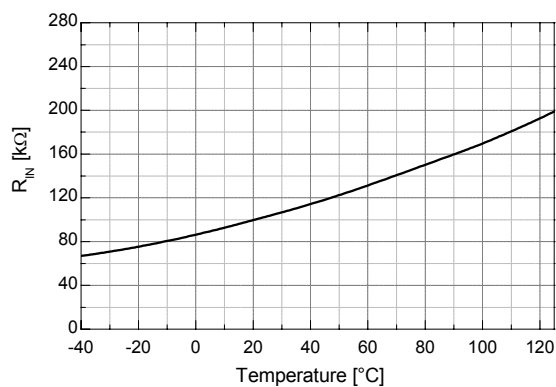


Figure 15. Input Pull-down Resistance vs. Temp.

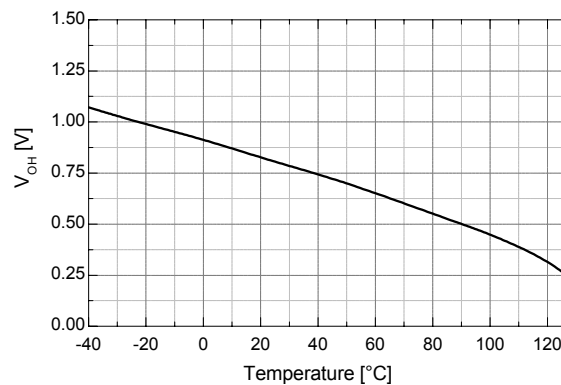


Figure 16. High-Level Output Voltage vs. Temp.

Typical Characteristics (Continued)

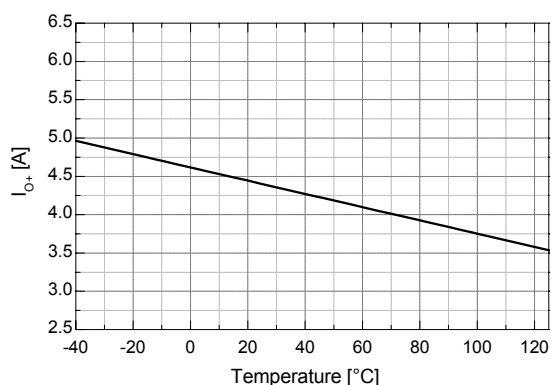


Figure 17. Output High, Short-Circuit Pulsed Current vs. Temp.

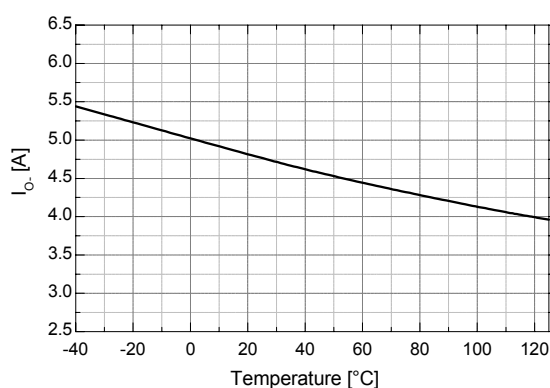


Figure 18. Output Low, Short-Circuit Pulsed Current vs. Temp.

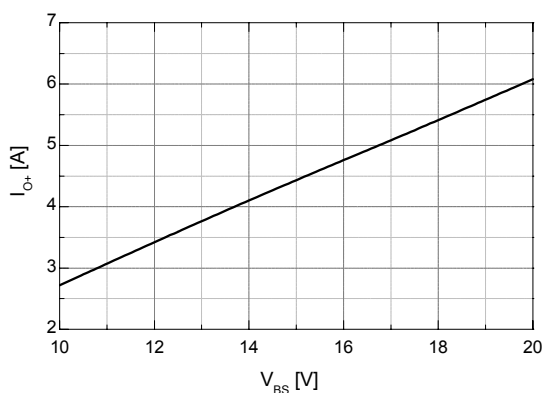


Figure 19. Output High, Short-Circuit Pulsed Current vs. Supply Voltage

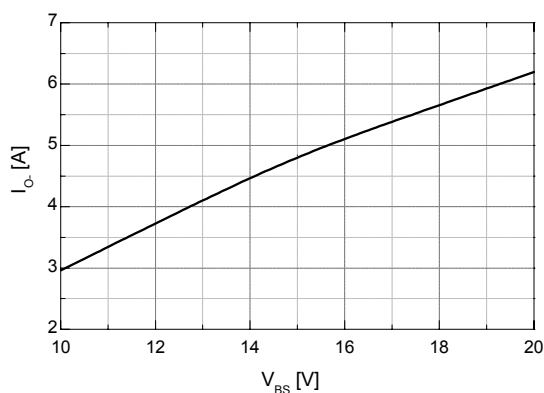
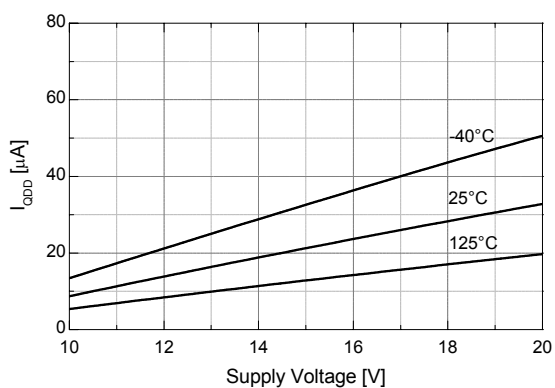
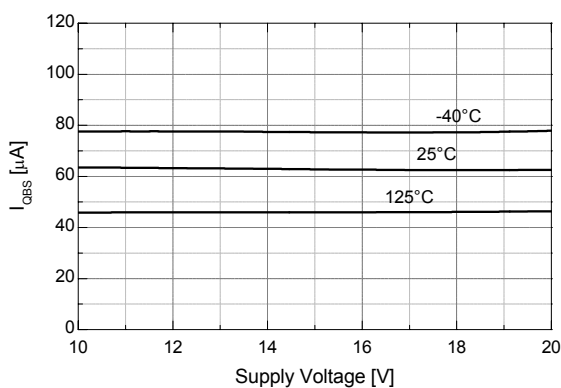


Figure 20. Output Low, Short-Circuit Pulsed Current vs. Supply Voltage

Figure 21. Quiescent V_{DD} Supply Current vs. Supply VoltageFigure 22. Quiescent V_{BS} Supply Current vs. Supply Voltage

Switching Time Definitions

Timing Diagram

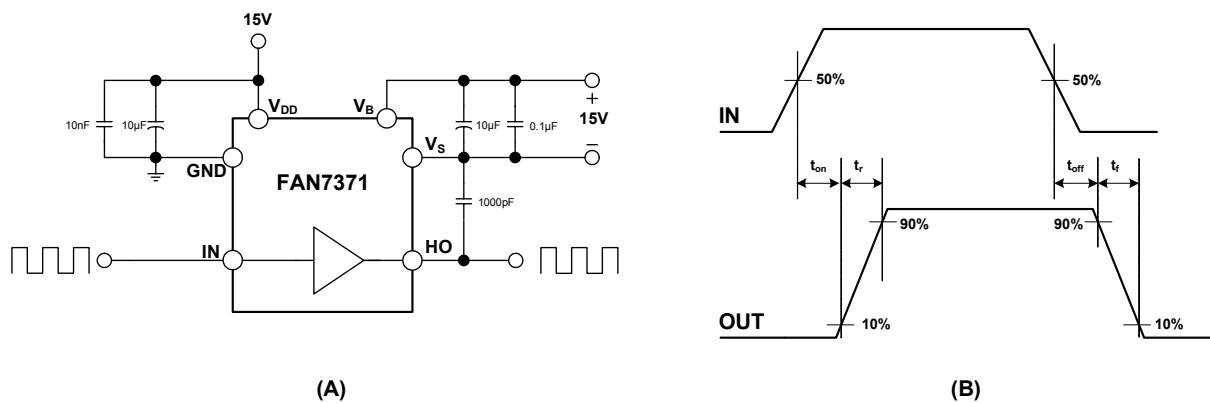


Figure 23. Switching Time Test Circuit and Waveform Definitions



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